

ICSSSTUB32S869B Advance Information

14-Bit Configurable Registered Buffer for DDR2

Recommended Application:

- DDR2 Memory Modules
- Provides complete DDR DIMM solution with ICS97U877
- Ideal for DDR2 400, 533 and 667

Product Features:

- 14-bit 1:2 registered buffer with parity check functionality
- Supports SSTL_18 JEDEC specification on data inputs and outputs
- 50% more dynamic driver strength than standard SSTU32864
- Supports LVCMOS switching levels on C1 and RESET# inputs
- Low voltage operation V_{DD} = 1.7V to 1.9V
- Available in 150 BGA package
- Green packages available

		Pin Configuration									
	1	2	3	4	5	6	7	8	9	10	11
А		0	0	0	0	0	0	0	0	0	0
в	0		0	0	0	0	0	0	0		0
С	0	0		0		0		0		0	0
D	0	0	0		0		0		0	0	0
Е	0	0		0		0		0		0	0
F	0	0	0		0		0		0	0	0
G	0	0	0	0		0		0	0	0	0
н	0		0		0		0		0		0
J	0	0		0		0		0		0	0
к	0	0	0	0				0	0	0	0
L	0	0		0		0		0		0	0
М	0		0		0		0		0		0
Ν	0	0	0	0		0		0	0	0	0
Р	0	0	0		0		0		0	0	0
R	0	0		0		0		0		0	0
т	0	0	0		0		0		0	0	0
U	0	0		0		0		0		0	0
v	0		0	0	0	0	0	0	0		0
w	0	0	0	0	0	0	0	0	0	0	
	-										

150 Ball BGA (Top View)

		In	puts				Outputs	
RESET#	DCS#	CSR#	СК	CK#	Dn, DODT, DCKE	Qn	QCS#	QODT, QCKE
Н	L	L	\uparrow	\downarrow	L	L	L	L
Н	L	L	\uparrow	\downarrow	Н	Н	L	Н
Н	L	L	L or H	L or H	Х	Q0	Q0	Q ₀
Н	L	Н	\uparrow	\downarrow	L	L	L	L
Н	L	Н	\uparrow	\downarrow	Н	Н	L	Н
Н	L	Н	L or H	L or H	Х	Q ₀	Q ₀	Q ₀
Н	Н	L	\uparrow	\downarrow	L	L	Н	L
Н	Н	L	\uparrow	\downarrow	Н	Н	Н	Н
Н	Н	L	L or H	L or H	Х	Q ₀	Q ₀	Q ₀
Н	Н	Н	\uparrow	\downarrow	L	Q ₀	Н	L
Н	Н	Н	\uparrow	\downarrow	Н	Q ₀	Н	Н
Н	Н	Н	L or H	L or H	Х	Q ₀	Q ₀	Q ₀
L	X or floating	L	L	L				

Functionality Truth Table

Ball Assignments

	1	2	3	4	5	6	7	8	9	10	11
А	NB	VDD	MCL ⁽¹⁾	NC	GND	VREF	GND	NC	MCL ⁽¹⁾	VDD	NC
В	VDD	NB	VDD	GND	GND	GND	GND	GND	VDD	NB	VDD
С	QCKEA	VDD	NB	GND	NB	GND	NB	GND	NB	VDD	QCKEB
D	Q2A	VDD	GND	NB	DCKE	NB	D2	NB	GND	VDD	Q2B
Е	Q3A	VDD	NB	D3	NB	NC	NB	DODT	NB	NC	Q3B
F	QODTA	VDD	GND	NB	NC	NB	NC	NB	GND	VDD	QODTB
G	Q5A	VDD	GND	D5	NB	CLK	NB	D6	GND	VDD	Q5B
Н	Q6A	NB	GND	NB	NC	NB	NC	NB	GND	NB	Q6B
J	QCSA#	VDD	NB	NC	NB	RESET#	NB	CSR#	NB	VDD	QCSB#
Κ	VDD	VDD	GND	GND	NB	NB	NB	GND	VDD	VDD	VDD
L	Q8A	VDD	NB	DCS#	NB	CLK#	NB	D8	NB	VDD	Q8B
М	Q9A	NB	GND	NB	NC	NB	NC	NB	GND	NB	Q9B
Ν	Q10A	VDD	GND	D9	NB	NC	NB	D10	GND	VDD	Q10B
Р	Q11A	VDD	GND	NB	NC	NB	NC	NB	GND	VDD	Q11B
R	Q12A	C1	NB	D11	NB	NC	NB	D12	NB	VDD	Q12B
Т	Q13A	VDD	GND	NB	D13	NB	D14	NB	GND	VDD	Q13B
U	Q14A	VDD	NB	GND	NB	GND	NB	GND	NB	VDD	Q14B
V	VDD	NB	VDD	GND	GND	GND	GND	GND	VDD	NB	VDD
W	P TYERR1#	VDD	MCL ⁽¹⁾	PARIN1	GND	VREF	GND	PPO1	MCL ⁽¹⁾	VDD	NB

Note: NC denotes a no-connect (ball present but not connected to the die). NB indicates no ball is populated at that gridpoint.

			Inp	uts			(Dutput
RESET#	DCS#	CSR#	СК	CK#	£ of inputs = H D1D14 ⁽¹⁾	PARIN1 ⁽²⁾	PPO1 ⁽²⁾	PTYERR1# ⁽³⁾
Н	L	Х	↑	\downarrow	Even	L	L	Н
Н	L	Х	↑	\rightarrow	Odd	L	Н	L
Н	L	Х	↑	\rightarrow	Even	Н	Н	L
Н	L	Х	1	\rightarrow	Odd	Н	L	Н
Н	L	L	↑	\downarrow	Even	L	L	Н
Н	L	L	↑	\rightarrow	Odd	L	Н	L
Н	L		1	\rightarrow	Even	Н	Н	L
Н	L	L	↑	\rightarrow	Odd	Н	L	Н
Н	Н	Н	↑	\rightarrow	Х	Х	PPOn ₀	PTYERRn₀#
Н	Х	Х	L or H	L or H	Х	Х	PPOn ₀	PTYERRn₀#
L	X or floating	X or floating	L	н				

Parity and Standby Function Table

NOTE 1 Inputs D1, D4 and D4 are not included in this range.

NOTE 2 PARIN1 arrives one (C1 = 0) or two (C = 1) clock cycles after data to which it applies.

NOTE 3 This transition assumes PTYERR1# is high at the crossing of CK going high and CK# going low. If PTYERR1# is low, it stays latched low for two clock cycles or until RESET# is driven low. PARIN1 is used to generate PPO1 and PTYERR1#.

General Description

The **ICSSSTUB32S869B** is 14-bit 1:2 registered buffer with parity is designed for 1.7 V to 1.9 V VDD operation. All clock and data inputs are compatible with the JEDEC standard for SSTL_18. The control inputs are LVCMOS. All outputs are 1.8 V CMOS drivers optimized to drive the DDR2 DIMM load. They provide 50% more dynamic driver strength than the standard SSTU32864 outputs.

The **ICSSSTUB32S869B** operates from a differential clock (CK and CK). Data are registered at the crossing of CK going high, and CK going low.

The device supports low-power standby operation. When the reset input (RESET) is low, the differential input receivers are disabled, and undriven (floating) data, clock and reference voltage (VREF) inputs are allowed. In addition, when RESET is low all registers are reset, and all outputs except PTYERR1# are forced low. The LVCMOS RESET input must always be held at a valid logic high or low level.

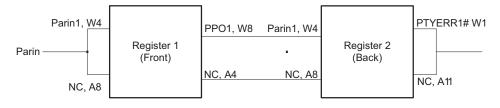
To ensure defined outputs from the register before a stable clock has been supplied, RESET must be held in the low state during power up.

In the DDR2 RDIMM application, RESET is specified to be completely asynchronous with respect to CK and CK. Therefore, no timing relationship can be guaranteed between the two. When entering reset, the register will be cleared and the outputs will be driven low quickly, relative to the time to disable the differential input receivers. However, when coming out of reset, the register will become active quickly, relative to the time to enable the differential input receivers. **ICSSSTUB32S869B** must ensure that the outputs remain low as long as the data inputs are low, the clock is stable during the time from the low-to-high transition of RESET and the input receivers are fully enabled. This will ensures that there are no glitches on the output.

The device monitors both DCS and CSR inputs and will gate the Qn, PPO1 (Paritial-Parity-Out) and PTYERR1# (Parity Error) Parity outputs from changing states when both DCS and CSR are high. If either DCS or CSR input is low, the Qn, PPO1 and PTYERR1# outputs will function normally. The RESET input has priority over the DCS and CSR controls and will force the Qn and PPO outputs low and the PTYERR1# high.

The **ICSSSTUB32S869B** includes a parity checking function. The **ICSSSTUB32S869B** accepts a parity bit from the memory controller at its input pin PARIN1 one or two cycles after the corresponding data input, compares it with the data received on the D-inputs and indicates on its opendrain PTYERR1 pin (active low) whether a parity error has occurred. The number of cycles depends on the setting of C1, see Figure 6 and 7.

When used as a single device, the C1 input is tied low. When used in pairs, the C1 inputs is tied low for the first register (front) and the C1 input is tied high for the second register. When used as a single register, the PPO1 and PTYERR1# signals are produced two clock cycles after the corresponding data input. When used in pairs, the PTYERR1# signals of the first register are left floating. The PPO1 outputs of the first register are cascaded to the PARIN1 signals on the second register (back). The PPO1 and PTYERR1# signals of the second register are produced three clock cycles after the corresponding data input. Parity implimentation and device wiring for single and dual die is described in Figure 1. If an error occurs, and the PTYERR1# is driven low, it stays low for two clock cycles or until RESET is driven low. The DIMM-dependent signals (DCKE, DCS, CSR and DODT) are not included in the parity check computations. All registers used on an individual DIMM must be of the same configuration, i.e single or dual die.



Set C1 = 0 for Register 1; Set C1 = 1 for Register 2. NC denotes No Connect.

Figure 1 - Parity implementation and device wiring for SSTU32S869 and SSTU32D869

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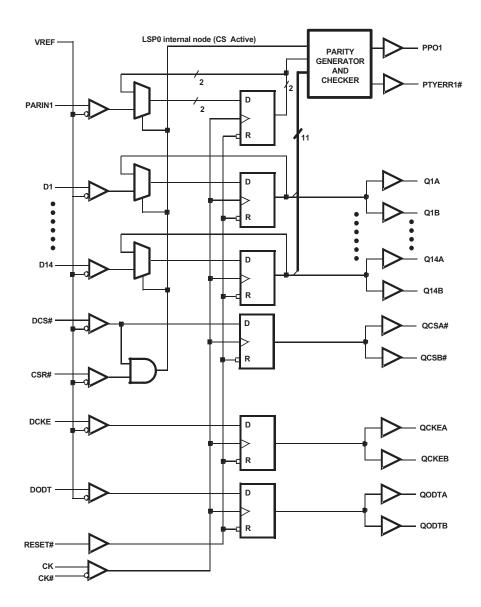
Terminal Functions

Signal Group	Signal Name	Туре	Description
Ungated inputs	DCKE, DODT	SSTL_18	DRAM function pins not associated with Chip Select.
Chip Select gated inputs	D1 D14 ⁽¹⁾	SSTL_18	DRAM inputs, re-driven only when Chip Select is LOW.
Chip Select inputs	DCS#, CSR#	SSTL_18	DRAM Chip Select signals. This pins initiate DRAM address/ command decodes, and as such at least one will be low when a valid address/command is present.
Re-driven outputs	Q1AQ14A, Q1BQ14B, QCSA#, QCSB# QCKEA,QCKEB QODTA,QODTB	SSTL_18	Outputs of the register, valid after the specified clock count and immediately following a rising edge of the clock.
Parity input	PARIN1	SSTL_18	Inout parity is received on pin PARIN1 and should maintain parity across the D1D14 ⁽¹⁾ inputs, at the rising edge of the clock, one cycle after Chip Select is LOW.
Parity output	PPO1	SSTL_18	Partial Parity Output. Indicates parity out of D1-D14 ⁽¹⁾
Parity error output	PTYERR1#	Open drain	When LOW, this output indicates that a parity error was identified associated with the address and/or command inputs. PTYERR1# will be active for two clock cycles, and delayed by in total 2 clock cycles for compatibility with final parity out timing on the industry-standard DDR2 register with parity (in JEDEC definition).
Configuration Inputs	C1	1.8V LVCMOS	When Low, register is configured as Register 1. When High, register is confugured as Register 2.
Clock inputs	CK, CK#	SSTL_18	Differential master clock input pair to the register. The register operation is triggered by a rising edge on the positive clock input (CK).
Miscellaneous inputs	RESET#	1.8 V LVCMOS	Asynchronous reset input. When LOW, it causes a reset of the internal latches, thereby forcing the outputs LOW. RESET# also resets the PTYERR# signal.
	VREF	0.9 V nominal	Input reference voltage for the SSTL_18 inputs. Two pins (internally tied together) are used for increased reliability.
	VDD	Power Input	Power supply voltage
	GND	Ground Input	Ground

NOTE 1 Inputs D1, D4 and D7 and their corresponding outputs Qn are not included in this range.

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Block Diagram

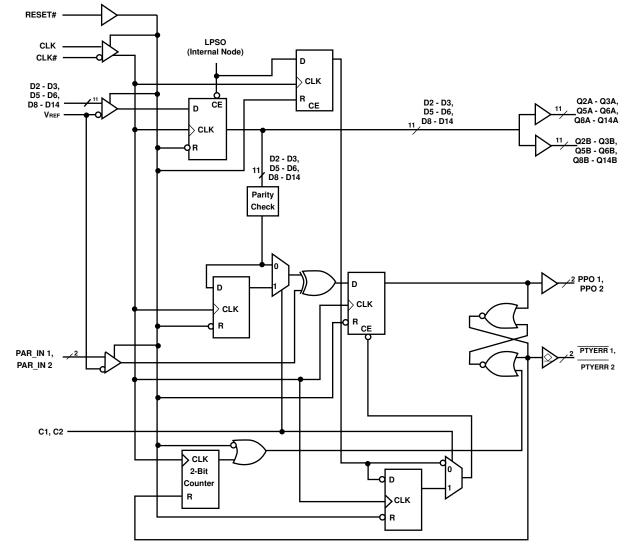


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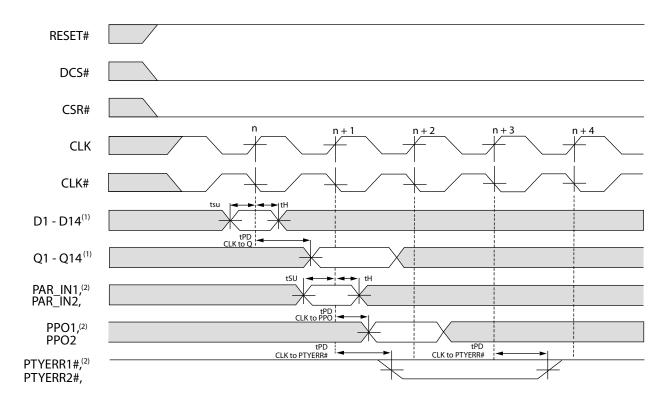
Block Diagram



NOTE 2 PARIN 1 is used to generate PPO1 and PTYERR1#.

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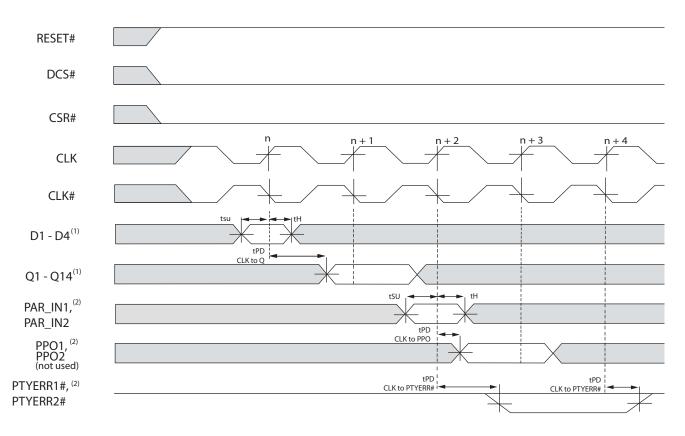
Register Timing



Note 1 This range doesn't include D1, D4 and D7 and their corresponding outputs

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Register Timing



Note 1: This range doesn't include D1, D4 and D7 and their corresponding outputs

Absolute Maximum Ratings

Storage Temperature	–65°C to +150°C
Supply Voltage	-0.5 to 2.5V
Input Voltage ¹	
Output Voltage ^{1,2}	-0.5 to VDDQ + 0.5
Input Clamp Current	
Output Clamp Current	±50mA
Continuous Output Current	±50mA
VDDQ or GND Current/Pin	±100mA
Package Thermal Impedance ³	36°C

Notes:

- The input and output negative voltage ratings may be excluded if the input and output clamp ratings are observed.
- This current will flow only when the output is in the high state level V₀ >V_{DDQ}.
- The package thermal impedance is calculated in accordance with JESD 51.

Stresses above those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only and functional operation of the device at these or any other conditions above those listed in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Recommended Operating Conditions

PARAMETER	DESCRIPTION		Min 🔿	TŶP	MAX	UNITS
V _{DD}	I/O Supply Voltage		1.7	1.8	1.9	
V _{REF}	Reference Voltage	$(C \wedge V)$	0.49 x V _{DD}	0.5 x V _{DD}	0.51 x V _{DD}	
Vπ	Termination Voltage		V _{REF} - 0.04	V _{REF}	V _{REF} + 0.04	
VI	Input Voltage	$\langle \rangle \rangle$ (0		V _{DDQ}	
V _{IH (DC)}	DC Input High Voltage	$\leq \langle \rangle$	V _{BEF} + 0.125	\diamond		
V _{IH (AC)}	AC Input High Voltage		V _{REF} + 0.250	//	$(\bigcirc)^{\vee}$	V
VIL (DC)	DC Input Low Voltage	Data Inputs			V _{REF} - 0.125	v
V _{IL (DC)}	AC Input Low Voltage				V _{REF} - 0.250	
V _{IH}	Input High Voltage Level	RESET#,	0.65 x V _{DDQ}]
V _{IL}	Input Low Voltage Level	CO			0.35 x V _{DDQ}]
V _{ICR}	Common mode Input Range		0.675	\checkmark	1.125]
V _{ID}	Differential Input Voltage	CLK, CLK#	0.600			
I _{OH}	High-Level Output Current Low-Level Output Current				-16	
I _{OL}					16	mA
T _A	Operating Free-Air Temperatu	ire	0		70	°C

¹Guaranteed by design, not 100% tested in production.

Note: Reset# and Cn inputs must be helf at valid logic levels (not floating) to ensure proper device operation. The differential inputs must not be floating unless Reset# is low.

Mode Select

C1	Device Mode
0	First Device in Pair, Front
1	Second Device in Pair, Back



Electrical Characteristics - DC

 $T_A = 0 - 70^{\circ}C$; $V_{DD} = 2.5 + -0.2V$, $V_{DDQ} = 2.5 + -0.2V$; (unless otherwise stated)

SYMBOL	PARAMETERS	CONDITIONS		V_{DDQ}	MIN	TYP	MAX	UNITS
VIK		I _I = -18mA					-1.2	
V		Ι _{ΟΗ} = -100μΑ		1.7V	V _{DDQ} - 0.2			
V _{OH}		I _{OH} = -16mA		1.7V	1.2			V
V		I _{OL} = 100μA		1.7V			0.2	
V _{OL}		I _{OL} = 16mA		1.7V			0.5	
կ	All Inputs	$V_{I} = V_{DD}$ or GND		1.9V			±5	μA
	Standby (Static)	RESET# = GND					0.2	μA
I _{DD}	Operating (Static)	$V_{I} = V_{IH(AC)} \text{ or } V_{IL(AC)},$ RESET# = V_{DD}		1.9V		TBD	2	mA
(clock only)	Dynamic operating (clock only)	$\label{eq:RESET} \begin{split} &RESET\# = V_{DD}, \\ &V_{I} = V_{IH(AC)} \text{ or } V_{IL(AC)}, \\ &CLK \text{ and } CLK\# \text{ switching} \\ &50\% \text{ duty cycle.} \end{split}$	1 ₀ = 0			TBD		µ/clock MHz
	Dynamic Operating (per each data input)	$\begin{split} \text{RESET#} &= V_{\text{DD}}, \\ V_{\text{I}} &= V_{\text{IH(AC)}} \text{ or } V_{\text{IL (AC)}}, \\ \text{CLK and CLK# switching} \\ 50\% \text{ duty cycle. One data} \\ \text{input switching at half} \\ \text{clock frequency, 50\%} \\ \text{duty cycle} \end{split}$		1.8V		TBD		µA/ clock MHz/data
	Input capacitance, D _n , PAR_IN inputs	V ₁ = V _{REF} ± 250 mV	$\mathcal{N}(\mathcal{C})$		2.5		3.5	pF
	Input capacitance, DCS#n	$V_1 = V_{BEF} \pm 250 \text{ mV}$		1.8V	2	D	3	pF
Ci	Input capacitance, CK and CK# inputs ²	$V_{ICR} = 0.9V; V_{I(PP)} = 600 \text{ mV}$ $V_{I} = V_{DD} \text{ or GND}$			2	\rightarrow	3	pF
	Input capacitance, RESET# input				Note 2		Note 2	pF
	Data Inputs CLK and CLK#	$V_1 = V_{REF} \pm 350 mV$ $V_{1CR} = 1.25V, V_{1(PP)} = 360 m$	۱V		2.5 2		3.5 3	pF
	RESET#	$V_{L} = V_{DDQ}$ or GND				2.5		

Notes:

1 - Guaranteed by design, not 100% tested in production.

2 - The vendor must supply this value for full device description.

Output Buffer Characteristics

Output edge rates over recommended operating free-air temperature range (See figure 7)

PARAMETER	V _{DD} = 1.8	3V ± 0.1V	UNIT		
FANAMETEN	MIN	МАХ	UNIT		
dV/dt_r	1	4	V/ns		
dV/dt_f	1	4	V/ns		
dV/dt_{Δ}^{1}		1	V/ns		

1. Difference between dV/dt_r (rising edge rate) and dV/dt_f (falling edge rate)

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Timing Requirements

(over recommended operating free-air temperature range, unless otherwise noted)

SYMBOL	PARAMETERS		$V_{DD} = 1.8$	3V ±0.1V	UNITS
STMBUL	PARAMETERS		MIN	MAX	UNITS
f _{clock}	Clock frequency			340	MHz
t _{ACT}	Differential inputs active time			10	ns
t _{INACT}	Differential inputs inactive time			15	ns
t _s	Setup time	Data before CLK \uparrow , CLK# \downarrow	0.5		
		DCS0 before CLK↑, CLK#↓, CSR# high	0.7	\square	ns
+	Hold time	DCS#, DODT, DCKE and Q after CK介, CK#↓	0.7		ns
t _H	Hold time	PARIN1 after CK↑, CK#↓	0.5		ns

Notes: 1 - Guaranteed by design, not 100% tested in production.

2 - For data signal input slew rate of 1V/ns.

3 - For data signal input slew rate of 0.5V/ns and < 1V/ns.

4 - CLK/CLK# signal input slew rate of 1V/ns.

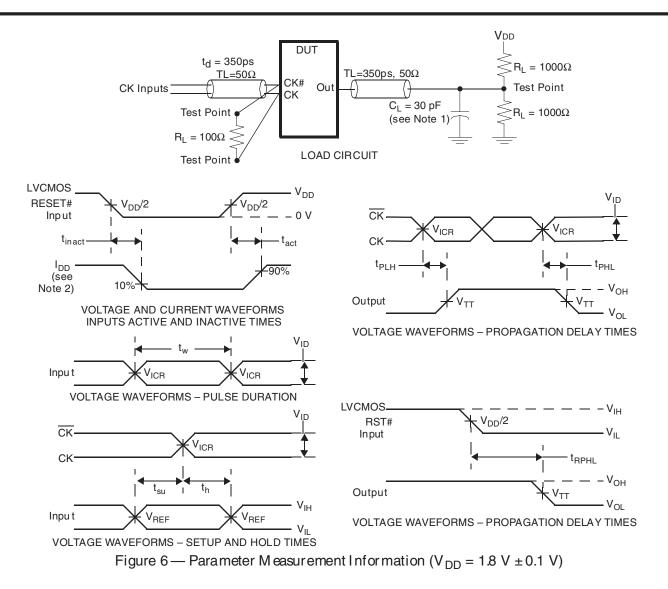
Switching Characteristics

(over recommended operating free-air temperature range, unless otherwise noted)

Symbol	Parameter	Measurement Conditions	MIN	мах	Units
fmax	Max input clock frequency		340	$\mathcal{O}_{\mathcal{A}}$	MHz
t _{PDM}	Propagation delay, single bit switching	CK↑ to CK#↓QN	1.2	1.9	ns
t _{LH}	Low to High propagation delay	CK1 to CK#↓to PTYERR#	1.2	3	ns
t _{HL}	High to low propagation delay	CK↑ to CK#↓to PTYERR#		3	ns
t _{PDMSS}	Propagation delay simultaneous switching	CK↑ to CK#↓QN	- Y	2	ns
t _{PHL}	High to low propagation delay	RESET#↓ to QN↓		3	ns
t _{PLH}	Low to High propagation delay	RESET#↓ to PTYERR1#↑		3	ns

1. Guaranteed by design, not 100% tested in production.

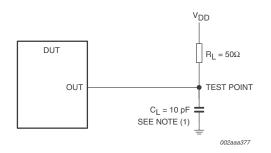
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- Notes: 1. CL incluces probe and jig capacitance.
 - 2. I_{DD} tested with clock and data inputs held at V_{DD} or GND, and Io = 0mA.
 - 3. All input pulses are supplied by generators having the following chareacteristics: PRR ≤ 0 MHz, Zo=50 Ω , input slew rate = 1 V/ns ±20% (unless otherwise specified).
 - 4. The outputs are measured one at a time with one transition per measurement.
 - 5. $V_{REF} = V_{DD}/2$
 - 6. $V_{IH} = V_{REF} + 250 \text{ mV}$ (ac voltage levels) for differential inputs. $V_{IH} = V_{DD}$ for LVCMOS input.
 - 7. VIL = VREF 250 mV (ac voltage levels) for differential inputs. VIL = GND for LVCMOS input.
 - 8. $V_{ID} = 600 \text{ mV}$
 - 9. t_{PLH} and t_{PHL} are the same as t_{PDM} .

Output slew rate measurement information ($V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}$)

All input pulses are supplied by generators having the following characteristics: PRR 10 MHz; $Z_0 = 50$; input slew rate = 1 V/ns ± 20%, unless otherwise specified.



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(1) C<sub>L</sub> includes probe and jig capacitance.
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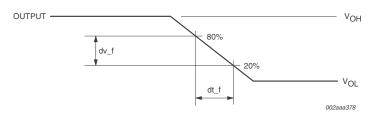
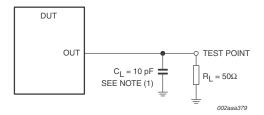
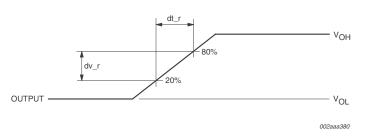


Figure 13 — Voltage waveforms, HIGH-to-LOW slew rate measurement





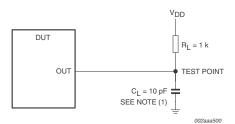






Error output load circuit and voltage measurement information (V_{DD} = 1.8 V \pm 0.1 V)

All input pulses are supplied by generators having the following characteristics: PRR10 MHz; $Z_0 = 50$; input slew rate = 1 V/ns \pm 20%, unless otherwise specified.



(1) C_L includes probe and jig capacitance.

Figure 16 — Load circuit, error output measurements

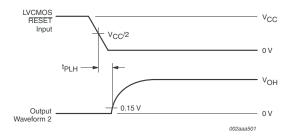


Figure 17 — Voltage waveforms, open-drain output LOW-to-HIGH transition time with respect to RESET# input

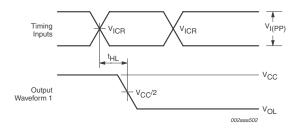


Figure 18 — Voltage waveforms, open-drain output HIGH-to-LOW transition time with respect to clock inputs

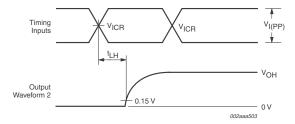
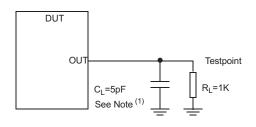


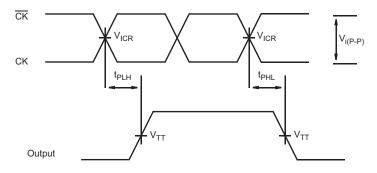
Figure 19 — Voltage waveforms, open-drain output LOW-to-HIGH transition time with respect to clock inputs

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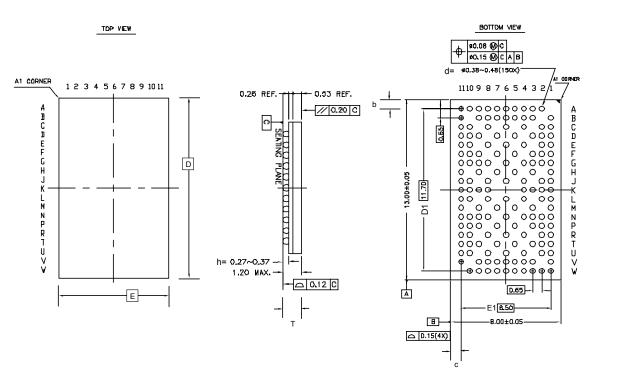
(1) C_L includes probe and jig capacitance.





$$\begin{split} &V_{TT} = V_{DD}/2 \\ &V_{ICR} \text{ Cross Point Voltage} \\ &V_{i(P-P)} = 600 \text{mV} \\ &t_{PLH} \text{ and } t_{PHL} \text{ are the same as } t_{PD}. \end{split}$$

Figure 23 — Partial parity out voltage waveform, propagation delay time with respect to CLK input



ALL DIMENSIONS IN MILLIMETERS

				BALL G RID							REF. DIMS		
D	Е	Т	е	HORIZ	VERT	TOTAL	d	h	D1	E1	b	с	
		Min/Max					Min/Max	Min/Max					
13.00 Bsc	8.00 Bsc	0.90/1.20	0.65 Bsc	11	19	150	0.38/0.48	0.27/0.37	11.70 Bsc	6.50 Bsc	0.65	0.75	***

Note: Ball grid total indicates maximum ball count for package. Lesser quantity may be used.

Ordering Information





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Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

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